

ASC600N1700MEDH

1700V, 600A, 4.3mΩ, Half-Bridge, Silicon Carbide MOSFET Module

Product Data Sheet

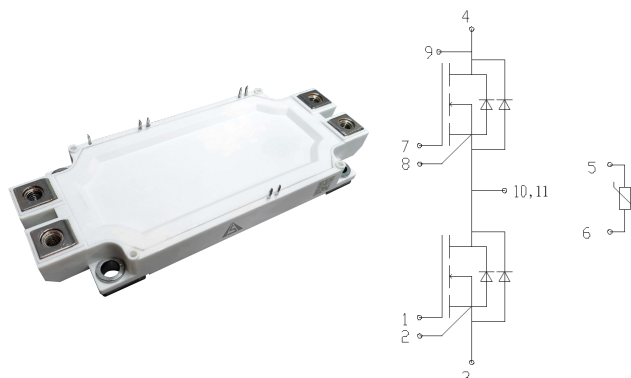
ASTC-3T03-129A A/0



爱仕特科技
AST TECHNOLOGY

General Description

AST MED series Silicon Carbide MOSFET module with AST 1700V Gen3 N-channel SiC MOSFET and SiC SBD. NTC temperature sensor inside.



Features

- High Temperature, Humidity, and Bias Operation
- Ultra Low Loss
- High-Frequency Operation
- Zero Turn-off Tail Current from MOSFET
- Normally-off, Fail-Safe Device Operation
- Copper Baseplate and Silicon Nitride Insulator



Applications

- High Power Converters
- Motor Drives
- Servo Drives
- UPS Systems
- Wind Turbines

Ordering Informations

Order Number / Marking	ASC600N1700MEDH
Package Type	MED

Key Parameters

Symbol	Parameter	Values			Unit	Test Conditions
Absolute maximum rating						
V _{DS}	Drain-Source Voltage	1700			V	T _C =25°C
I _D	Drain Current (continuous)	600			A	V _{GS} =18V; T _C =25°C
T _J	Junction Temperature	175			°C	
Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics						
R _{DS(on)}	Static Drain-Source on Resistance	-	4.3	5.0	mΩ	V _{GS} =18V; I _D =300A; T _C =25°C
Dynamic characteristics						
Q _G	Total Gate Charge	-	1008	-	nC	V _{DD} =1200V; V _{GS} =-5/+18V; I _D =300A; T _C =25°C
Q _{GD}	Gate-Drain Charge	-	300	-		
Source-drain diode						
Q _{RR}	Reverse Recovery Charge	-	5305	-	nC	V _{GS} =-5/+18V; I _F =300A; V _R =1200V; Load=100uH; T _J =25°C

Absolute Maximum Ratings (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	1700	V
V_{GS}	Gate-Source Voltage (dynamic)	-10/+22	V
I_D	Drain Current (continuous)	600	A
I_{DM}	Drain Current (pulsed)	1200	A
$T_{op}; T_{stg}$	Operating and Storage Temperature Range	-40 to +175	$^{\circ}\text{C}$
T_J	Junction Temperature	175	$^{\circ}\text{C}$
L_{Stray}	Stray Inductance	20	nH
V_{isol}	Isolation Test Voltage (DC; 2mA; t=10s)	4.2	kV
$R_{th Jh}$	Thermal Resistance, Junction-to-Heatsink	0.13	$^{\circ}\text{C/W}$

MOSFET Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
Static characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
BV_{DS}	Drain-Source Breakdown Voltage	1700	-	-	V	$V_{GS}=0\text{V}$
I_{DSS}	Zero Gate Voltage Drain Current	-	-	300	μA	$V_{DS}=1700\text{V}; V_{GS}=0\text{V}$
I_{GSS}	Gate-Body Leakage Current	-	-	3	μA	$V_{GS}=-10/20\text{V}; V_{DS}=0\text{V}$
$V_{GS(th)}$	Gate Threshold Voltage	2.0	-	4.0	V	$V_{DS}=V_{GS}; I_D=60\text{mA}$
$R_{DS(on)}$	Static Drain-Source on Resistance	-	4.3	5.0	$\text{m}\Omega$	$V_{GS}=18\text{V}; I_D=300\text{A}$
$V_{GS(on)}$	Recommended Turn-on Voltage	-	18	-	V	Static
$V_{GS(off)}$	Recommended Turn-off Voltage	-	-5	-	V	
R_G	Gate Resistance	-	0.58	-	Ω	$V_{AC}=25\text{mV}; f=1\text{MHz}$
Dynamic characteristics (at $T_c=25^{\circ}\text{C}$ unless otherwise specified)						
C_{iss}	Input Capacitance	-	38.8	-	nF	$V_{DS}=1200\text{V}; f=100\text{kHz}; V_{AC}=25\text{mV}$
C_{oss}	Output Capacitance	-	1.19	-		
C_{rss}	Reverse Transfer Capacitance	-	96	-	pF	
E_{on}	Turn-on Energy	-	24.4	-	mJ	$V_{DD}=1200\text{V}; V_{GS}=-5/+18\text{V}; I_D=300\text{A}; R_{G(ext)}=5\Omega; \text{Load}=100\mu\text{H}$
E_{off}	Turn-off Energy	-	16.2	-		
Q_{GS}	Gate-Source Charge	-	312	-	nC	$V_{DD}=1200\text{V}; V_{GS}=-5/+18\text{V}; I_D=300\text{A}$
Q_{GD}	Gate-Drain Charge	-	300	-		
Q_G	Total Gate Charge	-	1008	-		
$t_{d(on)}$	Turn-on Delay Time	-	89	-	ns	$V_{DD}=1200\text{V}; V_{GS}=-5/+18\text{V}; I_D=300\text{A}; R_{G(ext)}=5\Omega; \text{Load}=100\mu\text{H}$
t_r	Rise Time	-	68	-		
$t_{d(off)}$	Turn-off Delay Time	-	344	-		
t_f	Fall Time	-	83	-		

SiC Diode Characteristics (at T_J=25°C unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
V _{FSD}	Forward Voltage	-	-	1.9	V	V _{GS} =0V; I _F =300A
I _S	Continuous Diode Forward Current	-	300	-	A	V _{GS} =0V; T _C =100°C
t _{RR}	Reverse Recovery Time	-	85	-	ns	V _{GS} =-5/+18V; I _F =300A; V _R =1200V; Load=100μH
Q _{RR}	Reverse Recovery Charge	-	5305	-	nC	
I _{RRM}	Peak Reverse Recovery Current	-	150	-	A	

NTC Thermistor Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions
R ₂₅	Rated Resistance	-	5.00	-	kΩ	T _{NTC} =25°C
ΔR/R	Deviation of R ₁₀₀	-5	-	5	%	T _{NTC} =100°C; R ₁₀₀ =493.3Ω
B _{25/50}	Beta Value for 25°C to 50°C	-	3375	-	K	$R_2=R_{25} \exp[B_{25/50}(1/T_2 - 1/(298.15K))]$
B _{25/80}	Beta Value for 25°C to 80°C	-	3414	-	K	$R_2=R_{25} \exp[B_{25/80}(1/T_2 - 1/(298.15K))]$
B _{25/100}	Beta Value for 25°C to 100°C	-	3436	-	K	$R_2=R_{25} \exp[B_{25/100}(1/T_2 - 1/(298.15K))]$

Typical Performance

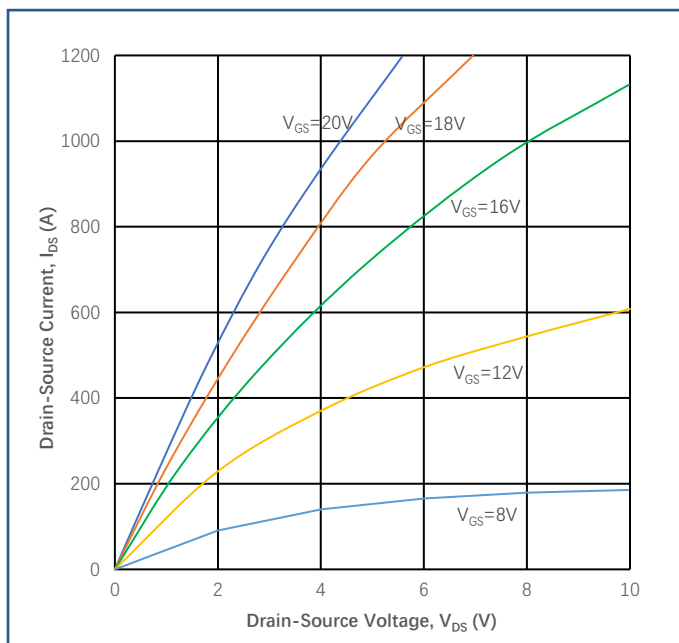


Figure 1
Output Characteristics ($T_J = 25^\circ\text{C}$)

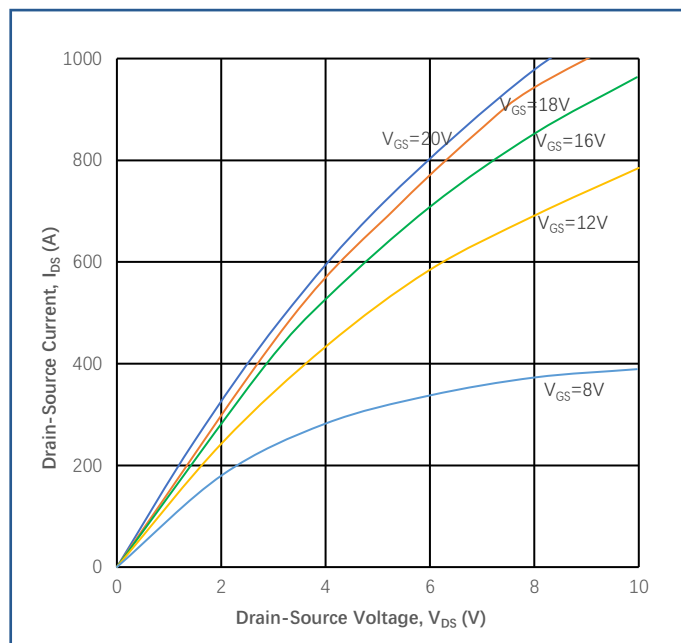


Figure 2
Output Characteristics ($T_J = 175^\circ\text{C}$)

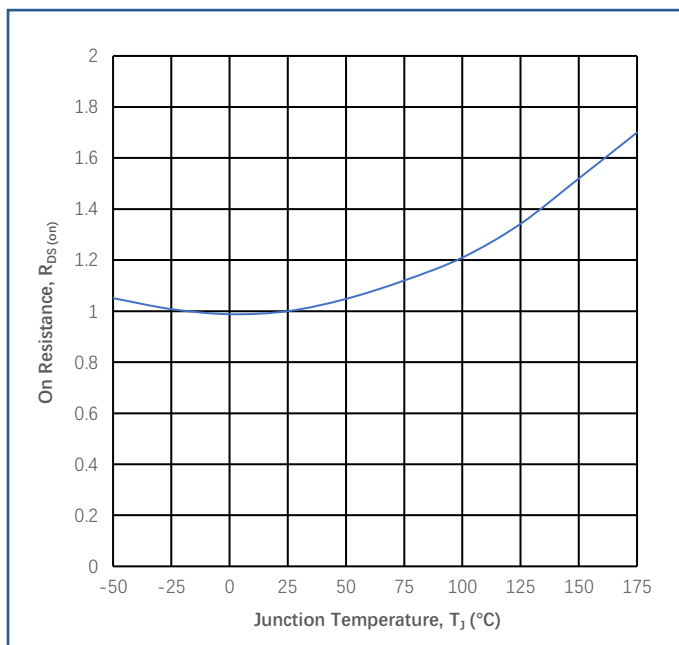


Figure 3
Normalized on-resistance vs. Temperature

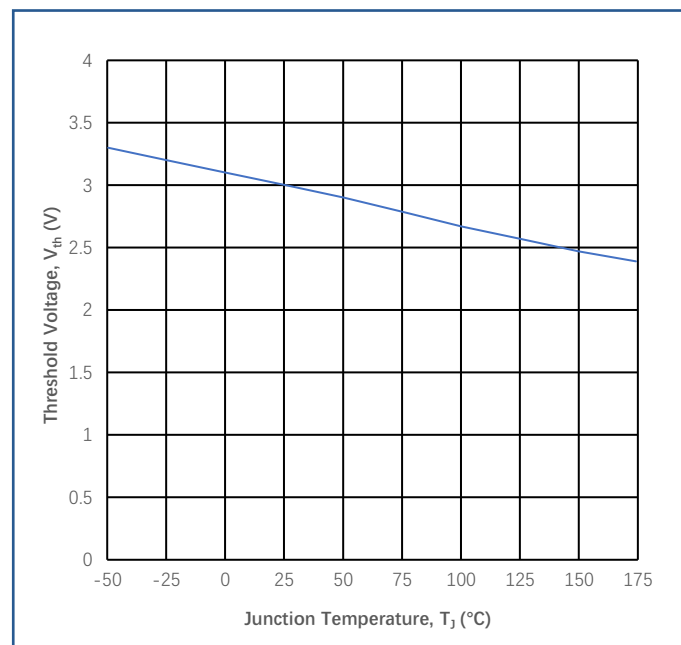


Figure 4
Threshold Voltage vs. Temperature

Typical Performance

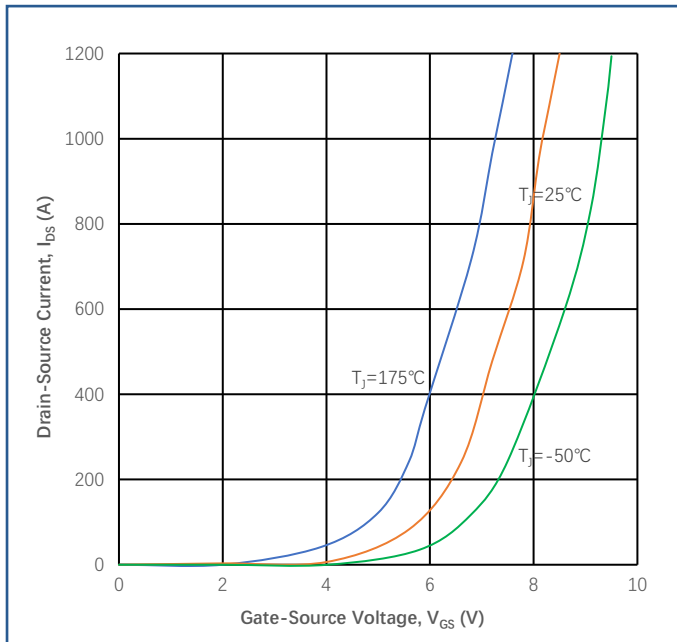


Figure 5

Transfer Characteristic for Various T_j

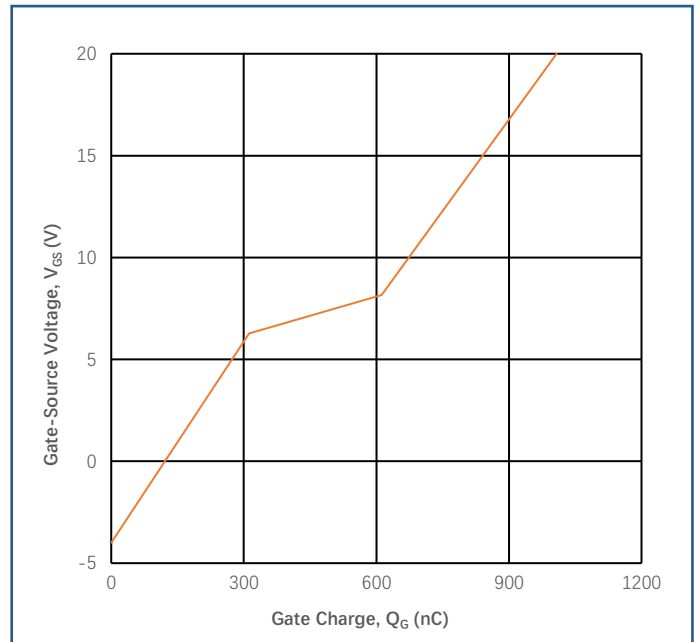


Figure 6

Typical Gate Charge Characteristics

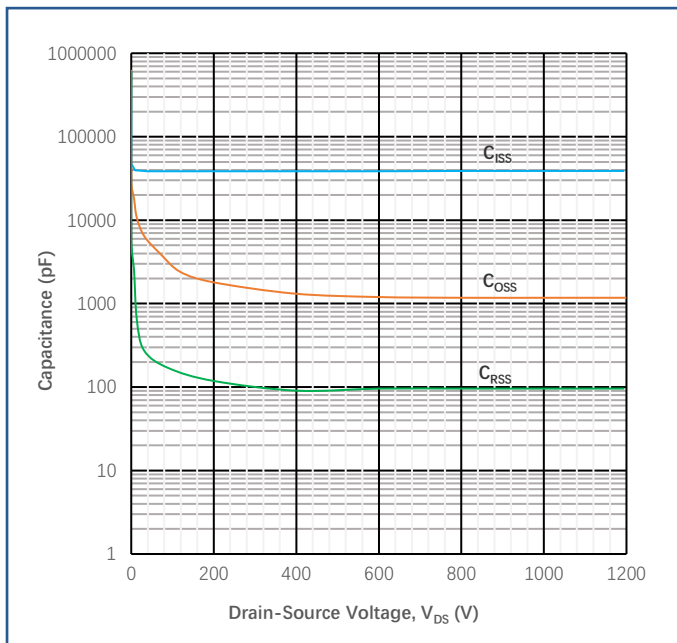


Figure 7

Typical Capacitances vs. Drain-Source Voltage

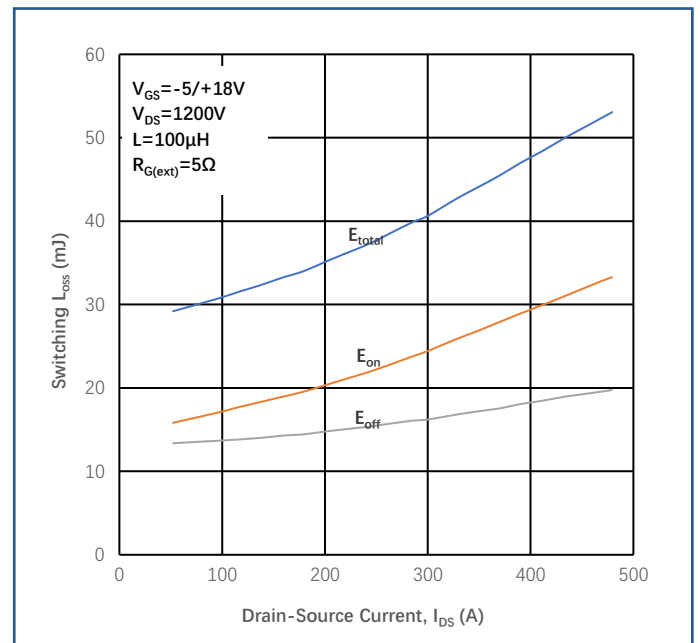


Figure 8

Inductive Switching Energy vs. Drain Current

Typical Performance

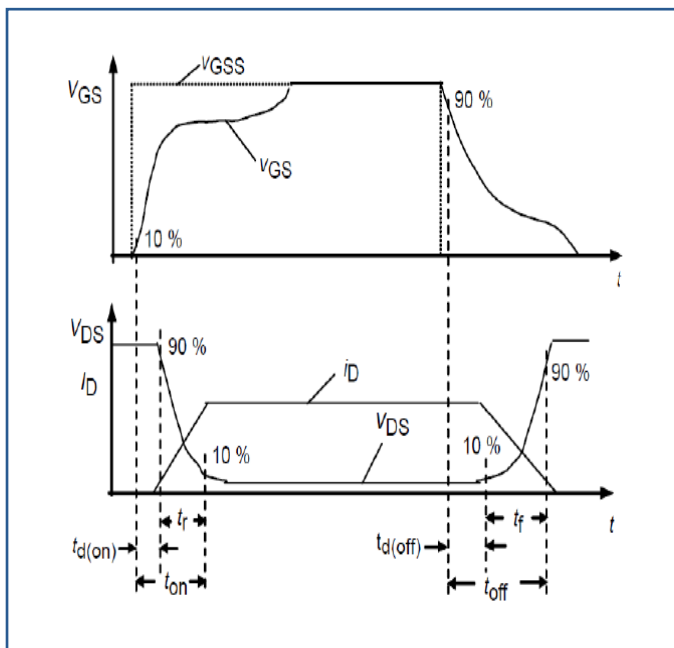


Figure 9

Switching Time Description

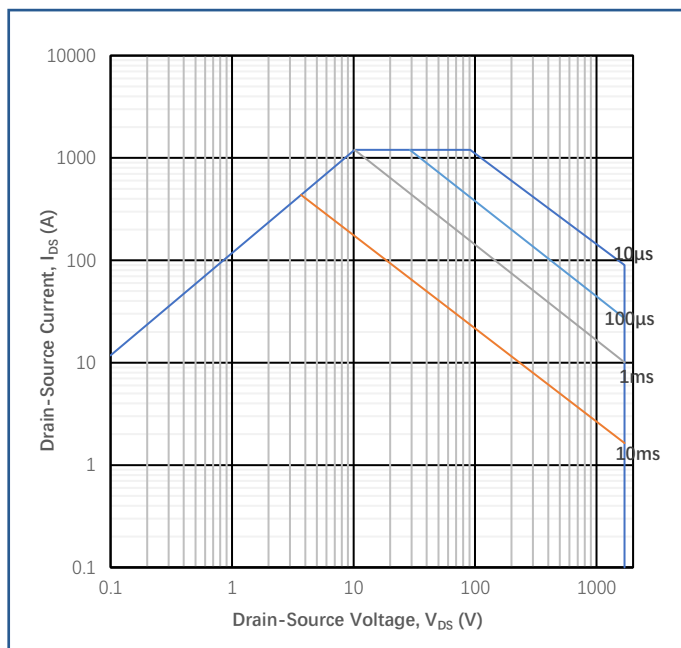
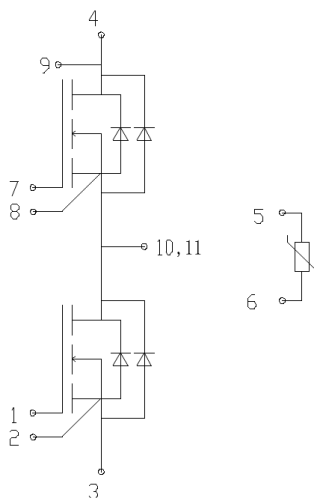


Figure 10

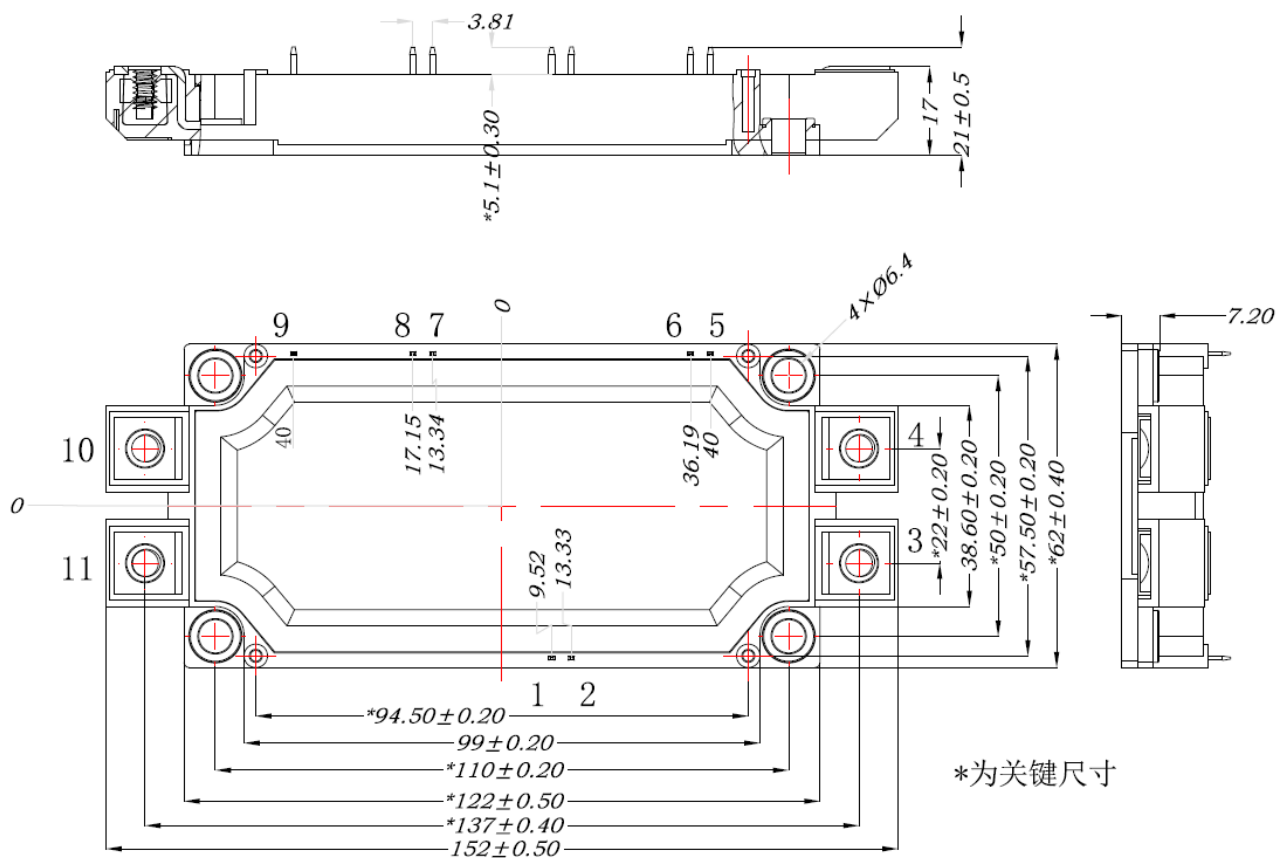
Safe Operating Area

Circuit Diagram Headline



Package Dimensions (mm)

Package Type: MED



未标注线性公差按 GB/1804-2000c 级执行	公差分段	0.5-3	3-6	6-30	30-120	120-400
	c 级	±0.2	±0.3	±0.5	±0.8	±1.2

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